## MMBD2835LT1G, MMBD2836LT1G, SMMBD2835LT1G

# Monolithic Dual Switching Diodes

## **Features**

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

## **MAXIMUM RATINGS (EACH DIODE)**

Rating	Symbol	Value	Unit
Reverse Voltage MMBD2835LT1G, SMMBD2835LT1G MMBD2836LT1G	V <sub>R</sub>	35 75	Vdc
Forward Current	lF	100	mAdc

#### THERMAL CHARACTERISTICS

Total Device Dissipation FR-5 Board (Note 1)  T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

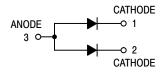


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SOT-23 (TO-236AB) CASE 318-08 STYLE 12



#### **MARKING DIAGRAM**



xxx = Specific Device Code A3X = MMBD2835LT1G SMMBD2835LT1G

A2X = MMBD2836LT1G = Date Code

M = Date Code

■ = Pb-Free Package (Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBD2835LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBD2835LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBD2836LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

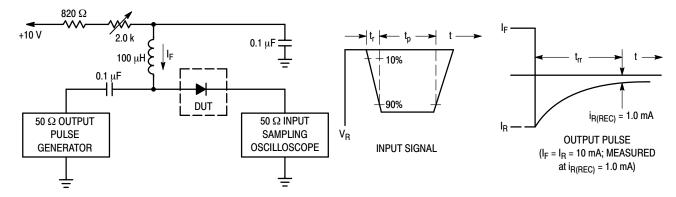
## MMBD2835LT1G, MMBD2836LT1G, SMMBD2835LT1G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•
Reverse Breakdown Voltage (I <sub>R</sub> = 100 μAdc) MMBD2835LT1G, SMMBD2835LT1G MMBD2836LT1G	V <sub>(BR)</sub>	35 75	- -	Vdc
Reverse Voltage Leakage Current (Note 3)  (V <sub>R</sub> = 30 Vdc)  MMBD2835LT1G, SMMBD2835LT1G  (V <sub>R</sub> = 50 Vdc)  MMBD2836LT1G	I <sub>R</sub>	-	100 100	nAdc
Diode Capacitance (V <sub>R</sub> = 0 V, f = 1.0 MHz)	C <sub>T</sub>	_	4.0	pF
Forward Voltage $(I_F = 10 \text{ mAdc})$ $(I_F = 50 \text{ mAdc})$ $(I_F = 100 \text{ mAdc})$	V <sub>F</sub>	- - -	1.0 1.0 1.2	Vdc
Reverse Recovery Time ( $I_F = I_R = 10 \text{ mAdc}$ , $I_{R(REC)} = 1.0 \text{ mAdc}$ ) (Figure 1)	t <sub>rr</sub>	-	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. For each individual diode while the second diode is unbiased.





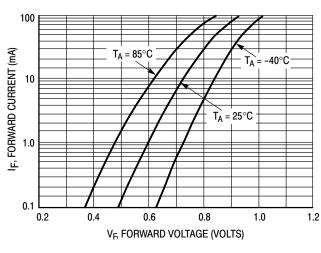
Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 10 mA.

- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA.
- 3.  $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

## MMBD2835LT1G, MMBD2836LT1G, SMMBD2835LT1G

## **CURVES APPLICABLE TO EACH CATHODE**



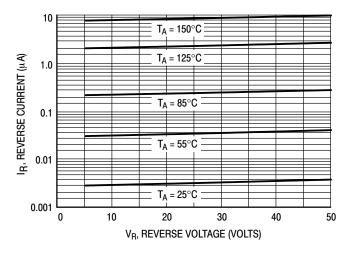


Figure 2. Forward Voltage

Figure 3. Leakage Current

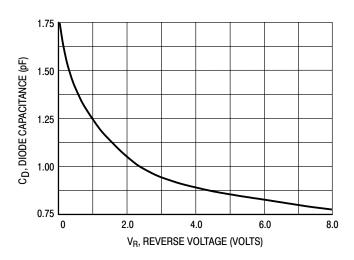


Figure 4. Capacitance

**MILLIMETERS** 

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

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## SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 

MAX

1.11

0.10

0.50

0.20

3.04

1.40

2.04

0.55

0.69

2.64

10°





DETAIL "A" Scale 3:1







### NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

## RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## **STYLES ON PAGE 2**

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

## SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR			
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	2. CATHODE 2.	2: STYLE 13: CATHODE PIN 1. SOURCE CATHODE 2. DRAIN ANODE 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	2. ANODE 2.	3: STYLE 19: NO CONNECTION PIN 1. CATHODE CATHODE 2. ANODE ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT			STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

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